

# Koji Muraki

## List of Publications by Year in descending order

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195  
papers

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docs citations

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times ranked

2703  
citing authors

#	ARTICLE	IF	CITATIONS
1	Gate tuning of fractional quantum Hall states in an InAs two-dimensional electron gas. Physical Review B, 2022, 105, .	3.2	2
2	Nonuniform heat redistribution among multiple channels in the integer quantum Hall regime. Physical Review B, 2022, 105, .	3.2	1
3	Quantized charge fractionalization at quantum Hall Y junctions in the disorder dominated regime. Nature Communications, 2021, 12, 131.	12.8	12
4	Screening Effects of Superlattice Doping on the Mobility of GaAs Two-Dimensional Electron System Revealed by in situ Gate Control. Physical Review Applied, 2021, 15, .	3.8	6
5	Cryogenic GaAs high-electron-mobility-transistor amplifier for current noise measurements. Review of Scientific Instruments, 2021, 92, 023910.	1.3	4
6	Andreev reflection of fractional quantum Hall quasiparticles. Nature Communications, 2021, 12, 2794.	12.8	20
7	Time-resolved investigation of plasmon mode along interface channels in integer and fractional quantum Hall regimes. Physical Review B, 2021, 104, .	3.2	4
8	Homemade-HEMT-based transimpedance amplifier for high-resolution shot-noise measurements. Review of Scientific Instruments, 2021, 92, 124712.	1.3	2
9	Sensitive current measurement on a quantum antidot with a Corbino-type electrode. Japanese Journal of Applied Physics, 2020, 59, SGGI03.	1.5	1
10	On-chip coherent frequency-domain THz spectroscopy for electrical transport. Applied Physics Letters, 2020, 117, .	3.3	9
11	Impact of epitaxial strain on the topological-nontopological phase diagram and semimetallic behavior of InAs/GaSb composite quantum wells. Physical Review B, 2020, 101, .	3.2	3
12	Suppression of gate screening on edge magnetoplasmons by highly resistive ZnO gate. Physical Review B, 2020, 101, .	3.2	6
13	Two-step breakdown of a local $\hat{\nu}=1$ quantum Hall state. Physical Review B, 2020, 101, .	3.2	4
14	Energy gap tuning and gate-controlled topological phase transition in InAs composite quantum wells. Physical Review Materials, 2020, 4, .	2.1	13
15	Determination of $\nu$ -factor in InAs two-dimensional electron system by capacitance spectroscopy. Applied Physics Express, 2019, 12, 063004.	2.4	7
16	Charge equilibration in integer and fractional quantum Hall edge channels in a generalized Hall-bar device. Physical Review B, 2019, 99, .	3.2	15
17	Surface-acoustic-wave resonators with Ti, Cr, and Au metallization on GaAs. Applied Physics Express, 2019, 12, 055001.	2.4	3
18	Spectroscopic study on hot-electron transport in a quantum Hall edge channel. Physical Review B, 2019, 99, .	3.2	19



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37	Evaluation of disorder introduced by electrolyte gating through transport measurements in graphene. <i>Applied Physics Express</i> , 2016, 9, 065102.	2.4	11
38	Andreev reflection and bound state formation in a ballistic two-dimensional electron gas probed by a quantum point contact. <i>Physical Review B</i> , 2016, 94, .	3.2	1
39	Publisher's Note: Electrical control of the sign of the factor in a GaAs hole quantum point contact [Phys. Rev. B 94, 041406(R) (2016)]. <i>Physical Review B</i> , 2016, 94, .	3.2	0
40	NMR probing of spin and charge order near odd-integer filling in the second Landau level. <i>Physical Review B</i> , 2015, 92, .	3.2	12
41	Exchange-Induced Spin Blockade in a Two-Electron Double Quantum Dot. <i>Physical Review Letters</i> , 2015, 115, 176802.	7.8	2
42	Gate-controlled semimetal-topological insulator transition in an InAs/GaSb heterostructure. <i>Physical Review B</i> , 2015, 91, .	3.2	38
43	Probing the extended-state width of disorder-broadened Landau levels in epitaxial graphene. <i>Physical Review B</i> , 2015, 92, .	3.2	14
44	Enhanced electron-phonon coupling for a semiconductor charge qubit in a surface phonon cavity. <i>Scientific Reports</i> , 2015, 5, 15176.	3.3	14
45	Self-aligned gate-all-around InAs/InP core-shell nanowire field-effect transistors. <i>Japanese Journal of Applied Physics</i> , 2015, 54, 04DN04.	1.5	5
46	Shot-Noise Evidence of Fractional Quasiparticle Creation in a Local Fractional Quantum Hall State. <i>Physical Review Letters</i> , 2015, 114, 056802.	7.8	20
47	Plasmon transport and its guiding in graphene. <i>New Journal of Physics</i> , 2014, 16, 063055.	2.9	10
48	Cross-correlation measurement of quantum shot noise using homemade transimpedance amplifiers. <i>Review of Scientific Instruments</i> , 2014, 85, 054704.	1.3	15
49	Spin-dependent tunneling rates for electrostatically defined GaAs quantum dots. <i>Physical Review B</i> , 2014, 90, .	3.2	6
50	Stable and unstable dynamics of Overhauser fields in a double quantum dot. <i>Physical Review B</i> , 2014, 89, .	3.2	4
51	Single-electron counting statistics with a finite frequency bandwidth. <i>Japanese Journal of Applied Physics</i> , 2014, 53, 04EJ01.	1.5	4
52	Fractionalized wave packets from an artificial Tomonaga-Luttinger liquid. <i>Nature Nanotechnology</i> , 2014, 9, 177-181.	31.5	107
53	NMR profiling of quantum electron solids in high magnetic fields. <i>Nature Physics</i> , 2014, 10, 648-652.	16.7	50
54	Transport Spectroscopy of Epitaxial Graphene on SiC Using Quantum Capacitances. , 2014, , .		1

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55	Plasmon transport in graphene investigated by time-resolved electrical measurements. Nature Communications, 2013, 4, 1363.	12.8	46
56	Real-space imaging of fractional quantum Hall liquids. Nature Nanotechnology, 2013, 8, 31-35.	31.5	36
57	Edge channel transport in the InAs/GaSb topological insulating phase. Physical Review B, 2013, 87, .	3.2	119
58	Distributed-element circuit model of edge magnetoplasmon transport. Physical Review B, 2013, 88, .	3.2	37
59	Intrinsic and extrinsic origins of low-frequency noise in GaAs/AlGaAs Schottky-gated nanostructures. Applied Physics Letters, 2013, 102, .	3.3	12
60	Transient Current in the Spin Blockade Region of a Double Quantum Dot. Japanese Journal of Applied Physics, 2013, 52, 110204.	1.5	1
61	Encapsulated gate-all-around InAs nanowire field-effect transistors. Applied Physics Letters, 2013, 103, .	3.3	18
62	$\nu = 1/2$ quantum Hall state in low-mobility electron systems: Different roles of disorder. Physical Review B, 2013, 88, .	3.2	38
63	Shot noise spectroscopy on a semiconductor quantum dot in the elastic and inelastic cotunneling regimes. Physical Review B, 2013, 87, .	3.2	29
64	Correlation of $1/f$ Noise between Semiconductor Point Contacts with a Common Lead. Japanese Journal of Applied Physics, 2012, 51, 02BJ08.	1.5	1
65	Frequency conversion of radio-frequency edge magnetoplasmons using a quantum point contact. Applied Physics Letters, 2012, 100, 233501.	3.3	4
66	Impact of graphene quantum capacitance on transport spectroscopy. Physical Review B, 2012, 86, .	3.2	26
67	Distributed electrochemical capacitance evidenced in high-frequency admittance measurements on a quantum Hall device. Physical Review B, 2012, 85, .	3.2	34
68	Magnetic-Field Dependence of Tunnel Couplings in Carbon Nanotube Quantum Dots. Physical Review Letters, 2012, 108, 176802.	7.8	30
69	Unraveling the Spin Polarization of the $\nu = 5/2$ Fractional Quantum Hall State. Science, 2012, 335, 828-831.	12.6	145
70	Field and Density Dependence of Edge Magnetoplasmon Transport in a Quantum Hall System. Journal of Physics: Conference Series, 2011, 334, 012032.	0.4	0
71	Spin-orbital Kondo effect in a parallel double quantum dot. Physical Review B, 2011, 84, .	3.2	30
72	Time Resolved Potential Measurement At Quantum Point Contacts Under Irradiation Of Surface Acoustic Burst Wave. , 2011, , .		3

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73	Gate-dependent spin-orbit coupling in multielectron carbon nanotubes. <i>Nature Physics</i> , 2011, 7, 348-353.	16.7	122
74	Interferometric detection of edge magnetoplasmons in AlGaAs/GaAs heterostructures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011, 8, 381-383.	0.8	4
75	Admittance Measurement for a Quantum Point Contact in a Multiterminal Quantum Hall Device. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 04DJ04.	1.5	3
76	Observation of Hysteretic Transport due to Dynamic Nuclear Spin Polarization in a GaAs Lateral Double Quantum Dot. <i>Physical Review Letters</i> , 2011, 107, 216802.	7.8	18
77	Gate-Dependent Orbital Magnetic Moments in Carbon Nanotubes. <i>Physical Review Letters</i> , 2011, 107, 186802.	7.8	20
78	Impact of Valley Polarization on the Resistivity in Two Dimensions. <i>Physical Review Letters</i> , 2011, 106, 196403.	7.8	8
79	Gate Operation of InAs/AlGaSb Heterostructures with an Atomic-Layer-Deposited Insulating Layer. <i>Applied Physics Express</i> , 2011, 4, 125702.	2.4	12
80	Density-Imbalance Stability Diagram of the $\nu = 1$ Bilayer Electron System at Full Spin Polarization. <i>Journal of Physics: Conference Series</i> , 2011, 334, 012025.	0.4	1
81	Admittance Measurement for a Quantum Point Contact in a Multiterminal Quantum Hall Device. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 04DJ04.	1.5	1
82	Crystallographic anisotropy of the Zeeman splitting in 1D hole quantum wires. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2010, 42, 967-970.	2.7	0
83	Low-temperature scanning tunneling microscopy of self-assembled InAs quantum dots grown by droplet epitaxy. <i>Physics Procedia</i> , 2010, 3, 1299-1304.	1.2	1
84	Fabrication and characterization of an undoped GaAs single hole transistor. , 2010, , .		0
85	Wide-band capacitance measurement on a semiconductor double quantum dot for studying tunneling dynamics. <i>Applied Physics Letters</i> , 2010, 96, 032104.	3.3	11
86	Intrinsic Gap and Exciton Condensation in the $\nu = 1$ Bilayer System. <i>Physical Review Letters</i> , 2010, 104, 056802.	7.8	17
87	Separately contacted monocrystalline silicon double-layer structure with an amorphous silicon dioxide barrier made by wafer bonding. <i>Semiconductor Science and Technology</i> , 2010, 25, 125001.	2.0	0
88	Voltage-controlled group velocity of edge magnetoplasmon in the quantum Hall regime. <i>Physical Review B</i> , 2010, 81, .	3.2	58
89	Fabrication and characterization of an induced GaAs single hole transistor. <i>Applied Physics Letters</i> , 2010, 96, 092103.	3.3	25
90	Room-temperature stability of Pt nanogaps formed by self-breaking. <i>Applied Physics Letters</i> , 2009, 94, .	3.3	52

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91	Electrons and holes in a 40 nm thick silicon slab at cryogenic temperatures. Applied Physics Letters, 2009, 94, 142104.	3.3	9
92	Electron-spin/nuclear-spin interactions and NMR in semiconductors. Semiconductor Science and Technology, 2009, 24, 023001.	2.0	34
93	SPIN EFFECTS IN THE PHASE TRANSITION OF THE $\nu = 1$ BILAYER ELECTRON SYSTEM. International Journal of Modern Physics B, 2009, 23, 2587-2595.	2.0	1
94	The interplay between one-dimensional confinement and two-dimensional crystallographic anisotropy effects in ballistic hole quantum wires. New Journal of Physics, 2009, 11, 043018.	2.9	21
95	NMR study of a canted antiferromagnet in a bilayer quantum Hall system. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 937-941.	2.7	1
96	Investigating the transport properties of the excitonic state in quasi-Corbino electron bilayers. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 1034-1037.	2.7	4
97	Metallic behavior in low-disorder two-dimensional hole systems in the presence of long- and short-range disorder. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 1599-1601.	2.7	0
98	Impact of long- and short-range disorder on the metallic behaviour of two-dimensional systems. Nature Physics, 2008, 4, 55-59.	16.7	39
99	Highly reproducible fabrication of back-gated GaAs/AlGaAs heterostructures using AuGeNi ohmic contacts with initial Ni layer. Applied Physics Letters, 2008, 92, .	3.3	8
100	The 0.7 anomaly in one-dimensional hole quantum wires. Journal of Physics Condensed Matter, 2008, 20, 164205.	1.8	10
101	Modulation of bilayer quantum Hall states by tilted-field-induced subband-Landau-level coupling. Physical Review B, 2008, 77, .	3.2	12
102	Spin-Dependent Phase Diagram of the $\nu = 1$ Bilayer Electron System. Physical Review Letters, 2008, 100, 106803.	7.8	36
103	Exciton condensate at a total filling factor of one in Corbino two-dimensional electron bilayers. Physical Review B, 2008, 77, .	3.2	37
104	Quantum transport in one-dimensional GaAs hole systems. International Journal of Nanotechnology, 2008, 5, 318.	0.2	1
105	INTERACTION OF ELECTRON AND NUCLEAR SPINS IN QUANTUM WELLS. International Journal of Modern Physics B, 2007, 21, 1266-1275.	2.0	0
106	NMR Evidence for Spin Canting in a Bilayer $\nu = 1$ Quantum Hall System. Physical Review Letters, 2007, 99, 076805.	7.8	42
107	Nuclear spin manipulation in semiconductor nanostructures. Proceedings of SPIE, 2007, , .	0.8	0
108	Conductance Quantisation In An Induced Hole Quantum Wire. AIP Conference Proceedings, 2007, , .	0.4	0

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109	Nuclear-spin-lattice relaxation in a bilayer quantum Hall system. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2006, 34, 164-167.	2.7	3
110	Electronic transport characteristics in a one-dimensional constriction defined by a triple-gate structure. <i>Journal of Applied Physics</i> , 2006, 100, 043701.	2.5	14
111	Low-Frequency Spin Dynamics in a Canted Antiferromagnet. <i>Science</i> , 2006, 313, 329-332.	12.6	50
112	Ballistic transport in induced one-dimensional hole systems. <i>Applied Physics Letters</i> , 2006, 89, 092105.	3.3	55
113	Fabrication of induced two-dimensional hole systems on (311)A GaAs. <i>Journal of Applied Physics</i> , 2006, 99, 023707.	2.5	30
114	Nanometre-scale nuclear-spin device for quantum information processing. <i>Journal of Physics Condensed Matter</i> , 2006, 18, S885-S900.	1.8	25
115	Fabrication and characterization of a 2D hole system in novel (311)A GaAs SISFET. <i>Microelectronics Journal</i> , 2005, 36, 327-330.	2.0	2
116	Controlled multiple quantum coherences of nuclear spins in a nanometre-scale device. <i>Nature</i> , 2005, 434, 1001-1005.	27.8	186
117	Resistance Oscillations by Electron-Nuclear Spin Coupling in Microscopic Quantum Hall Devices. <i>Japanese Journal of Applied Physics</i> , 2005, 44, 2669-2671.	1.5	0
118	In-plane field induced anisotropy of the longitudinal resistance in a bilayer quantum Hall system. <i>AIP Conference Proceedings</i> , 2005, . .	0.4	0
119	Self-Sustaining Resistance Oscillations by Electron-Nuclear Spin Coupling in Mesoscopic Quantum Hall Systems. <i>AIP Conference Proceedings</i> , 2005, . .	0.4	0
120	Effects of Inversion Asymmetry on Electron-Nuclear Spin Coupling in Semiconductor Heterostructures: Possible Role of Spin-Orbit Interactions. <i>Physical Review Letters</i> , 2005, 94, 146601.	7.8	16
121	Spin Degree of Freedom in the $\nu=1$ Bilayer Electron System Investigated by Nuclear Spin Relaxation. <i>Physical Review Letters</i> , 2005, 94, 096802.	7.8	53
122	Intralayer backscattering in narrow GaAs/AlxGa1-xAs/GaAs bilayer channels. <i>Physical Review B</i> , 2004, 69, .	3.2	2
123	Coulomb Drag as a Probe of the Nature of Compressible States in a Magnetic Field. <i>Physical Review Letters</i> , 2004, 92, 246801.	7.8	13
124	Self-sustaining resistance oscillations: Electron-nuclear spin coupling in mesoscopic quantum Hall devices. <i>Physical Review B</i> , 2004, 69, .	3.2	10
125	Phase diagrams of $\nu=2$ and $\nu=3$ quantum Hall states in bilayer systems. <i>Physical Review B</i> , 2004, 69, .	3.2	14
126	ANISOTROPIC TRANSPORT ON THE $\nu=1$ BILAYER QUANTUM HALL SYSTEM UNDER TILTED MAGNETIC FIELD. <i>International Journal of Modern Physics B</i> , 2004, 18, 3705-3708.	2.0	4



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127	DOUBLE MAGNETORESISTANCE MINIMA INDUCED BY THE IN-PLANE MAGNETIC FIELD FOR THE $\hat{\nu}=1$ DOUBLE-LAYER QUANTUM HALL STATE. International Journal of Modern Physics B, 2004, 18, 3709-3712.	2.0	2
128	Effects of in-plane magnetic fields on spin transitions in bilayer quantum Hall states. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 22, 36-39.	2.7	2
129	Simultaneous excitation of spins and pseudospins in the bilayer $\hat{\nu}=1$ quantum Hall state. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 22, 52-55.	2.7	17
130	Integer filling factor phases in vertical diatomic artificial molecules. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 22, 502-505.	2.7	0
131	Molecular phases in coupled quantum dots. Physical Review B, 2004, 69, .	3.2	58
132	Integer filling factor phases and isospin in vertical diatomic artificial molecules. Physical Review B, 2004, 70, .	3.2	13
133	Quantum Hall effects at Landau level crossings. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 20, 133-142.	2.7	4
134	Charge excitation and transport in pseudospin quantum Hall ferromagnets. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 18, 107-108.	2.7	0
135	Continuous transformation from spin- to pseudospin-type excitation. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 18, 118-119.	2.7	10
136	Pulsed-mode operation of nuclear spin polarization in integer quantum Hall systems. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 18, 128-129.	2.7	0
137	Density functional theory application to double quantum dots: Influence of mismatch on the addition energy spectra of vertical diatomic artificial molecules. International Journal of Quantum Chemistry, 2003, 91, 498-503.	2.0	3
138	Chaos and open orbits in hole-antidot arrays with non-isotropic Fermi surface. Europhysics Letters, 2003, 61, 382-388.	2.0	8
139	Vertical diatomic artificial molecule in the intermediate-coupling regime in a parallel and perpendicular magnetic field. Physical Review B, 2003, 67, .	3.2	26
140	Electronâ€Nuclear Spin Interaction in Edge States of Quantum Hall Systems. Journal of the Physical Society of Japan, 2003, 72, 44-48.	1.6	1
141	Phase Diagram of Interacting Composite Fermions in the Bilayer $\hat{\nu}=2/3$ Quantum Hall Effect. Physical Review Letters, 2002, 89, 116802.	7.8	20
142	Spin polarization of fractional quantum Hall edge channels studied by dynamic nuclear polarization. Physical Review B, 2002, 65, .	3.2	49
143	Electrically Controlled Nuclear Spin Polarization and Relaxation by Quantum-Hall States. Physical Review Letters, 2002, 88, 176601.	7.8	146
144	Activation studies of pseudospin quantum Hall ferromagnets in double quantum wells. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 12, 8-11.	2.7	7

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145	Spin polarization in fractional quantum Hall edge channels. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 12, 76-79.	2.7	2
146	Various phase transitions in bilayer quantum Hall states. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 12, 32-35.	2.7	1
147	Influence of mismatch on the addition energy spectra of vertical diatomic artificial molecules. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 12, 896-899.	2.7	2
148	Dynamic nuclear-spin polarization induced by scattering between fractional quantum Hall edge channels. Microelectronic Engineering, 2002, 63, 63-68.	2.4	0
149	Vertical diatomic artificial quantum dot molecules. , 2002, , 65-84.		0
150	Dissociation of Vertical Semiconductor Diatomic Artificial Molecules. Physical Review Letters, 2001, 87, 066801.	7.8	73
151	Magnetic field induced transitions in the few-electron ground states of artificial molecules. Solid State Communications, 2001, 119, 183-190.	1.9	37
152	Nonequilibrium population in fractional edge states. Physica B: Condensed Matter, 2001, 298, 150-154.	2.7	7
153	Preferred number of flipped spins in Skyrmion excitation. Physica B: Condensed Matter, 2001, 298, 169-172.	2.7	0
154	Scaling in fractional quantum Hall transitions. Physica B: Condensed Matter, 2001, 298, 182-186.	2.7	0
155	Longitudinal resistance anomaly around the $2/3$ filling factor observed in a GaAs/AlGaAs single heterostructure. Physica B: Condensed Matter, 2001, 298, 191-194.	2.7	12
156	Single dot and strongly coupled double dots at high magnetic fields. Physica E: Low-Dimensional Systems and Nanostructures, 2001, 10, 112-116.	2.7	10
157	Backgated layers and nanostructures. Physica E: Low-Dimensional Systems and Nanostructures, 2001, 11, 155-160.	2.7	1
158	Resistance fluctuations in quantum Hall transitions: Network of compressible-incompressible regions. Physical Review B, 2001, 63, .	3.2	26
159	Charge Excitations in Easy-Axis and Easy-Plane Quantum Hall Ferromagnets. Physical Review Letters, 2001, 87, 196801.	7.8	65
160	Doubly Enhanced Skyrmions in $\nu = 2$ Bilayer Quantum Hall States. Journal of the Physical Society of Japan, 2000, 69, 3178-3181.	1.6	14
161	Resistance fluctuations in integer quantum-Hall transitions. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 6, 152-155.	2.7	2
162	Quantum coherence and skyrmion textures in bilayer quantum Hall systems. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 6, 640-644.	2.7	0

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163	n+-GaAs Back-Gated Double-Quantum-Well Structures with Full Density Control. Japanese Journal of Applied Physics, 2000, 39, 2444-2447.	1.5	36
164	Spin transition of a two-dimensional hole system in the fractional quantum Hall effect. Physical Review B, 1999, 59, R2502-R2505.	3.2	11
165	Interlayer charge transfer in bilayer quantum Hall states at various filling factors. Solid State Communications, 1999, 112, 625-629.	1.9	24
166	High-quality two-dimensional electron gas at an inverted undoped heterointerface. Superlattices and Microstructures, 1999, 25, 295-300.	3.1	0
167	n-GaAs Back-Gated Double-Quantum-Well Structures with Full Density Control. , 1999, , .		1
168	Electronic states in quantum dot atoms and molecules. Physica E: Low-Dimensional Systems and Nanostructures, 1998, 3, 112-120.	2.7	37
169	Effect of valence band structure on the fractional quantum Hall effect of two-dimensional hole systems. Physica B: Condensed Matter, 1998, 249-251, 65-69.	2.7	5
170	Quantum dot molecules. Physica B: Condensed Matter, 1998, 249-251, 206-209.	2.7	129
171	Re-entrant behavior of the $\nu=4/3$ fractional quantum Hall effect in a front-and-back-gated 2D hole gas. Physica B: Condensed Matter, 1998, 256-258, 86-89.	2.7	1
172	Two-dimensional electron gas formed in a back-gated undoped heterostructure. Applied Physics Letters, 1998, 72, 1745-1747.	3.3	41
173	Metastability of the quantum Hall states in asymmetric two-layer systems. Journal of Physics Condensed Matter, 1998, 10, 8305-8311.	1.8	2
174	High-Mobility Two-Dimensional Electron Gas in an Undoped Heterostructure: Mobility Enhancement after Illumination. Japanese Journal of Applied Physics, 1998, 37, L765-L767.	1.5	15
175	Quantum Hall effect in asymmetric double quantum well systems. Semiconductor Science and Technology, 1998, 13, 296-301.	2.0	3
176	Photoluminescence from a modulation-doped $\text{Al}_{0.33}\text{Ga}_{0.67}\text{As}/\text{GaAs}$ heterointerface under cyclotron resonance. Physical Review B, 1998, 58, 15385-15388.	3.2	3
177	Splitting of resistance peaks and anomalous Hall plateaus in asymmetric double-quantum-well structures. Physical Review B, 1997, 56, 1057-1060.	3.2	10
178	The infrared vibrational absorption spectrum of the $\text{Si}^{\text{X}}$ defect present in heavily Si doped GaAs. Journal of Applied Physics, 1997, 82, 137-141.	2.5	16
179	Suppression of superlattice intermixing by p-type doping. Journal of Crystal Growth, 1997, 175-176, 162-167.	1.5	6
180	Evidence for resonant electron capture and charge buildup in $\text{GaAs}/\text{Al}_x\text{Ga}_{1-x}\text{As}$ quantum wells. Physical Review B, 1996, 53, 15477-15480.	3.2	7

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181	Growth of InGaAs/GaAs strained quantum wells on GaAs(111)B substrates and continuous wave operation of (111)-oriented InGaAs strained quantum well lasers. <i>Journal of Crystal Growth</i> , 1995, 150, 1338-1343.	1.5	10
182	Observation of spatially-indirect transition and accurate determination of band offset ratio by excitation spectroscopy on GaAs/AlGaAs quantum wells lightly doped with Be acceptors. <i>Journal of Crystal Growth</i> , 1995, 150, 49-53.	1.5	4
183	Enhancement of nonradiative recombination due to resonant electron capture in Al <sub>x</sub> Ga <sub>1-x</sub> As/GaAs quantum-well structures. <i>Physical Review B</i> , 1995, 51, 14324-14329.	3.2	8
184	Time-of-flight measurement of carrier transport and carrier collection in strained Si <sub>1-x</sub> Ge <sub>x</sub> /Si quantum wells. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1994, 12, 1156.	1.6	13
185	Direct observation of exciton localization in a GaAs/AlGaAs quantum well. <i>Applied Physics Letters</i> , 1994, 64, 1845-1847.	3.3	10
186	Valence-subband level crossing in GaAs/GaAsP strained-barrier quantum well structures observed by circularly polarized photoluminescence excitation spectroscopy. <i>Solid-State Electronics</i> , 1994, 37, 915-918.	1.4	0
187	Enhancement of free-to-bound transitions due to resonant electron capture in Be-doped AlGaAs/GaAs quantum wells. <i>Solid-State Electronics</i> , 1994, 37, 1247-1250.	1.4	6
188	In-plane transport of excitons in quantum well structures. <i>Solid State Communications</i> , 1993, 88, 677-681.	1.9	10
189	Surface segregation of In atoms and its influence on the quantized levels in InGaAs/GaAs quantum wells. <i>Journal of Crystal Growth</i> , 1993, 127, 546-549.	1.5	68
190	Fast Lateral Transport of Excitons in a GaAs/AlGaAs Quantum Well. <i>Japanese Journal of Applied Physics</i> , 1993, 32, 5586-5590.	1.5	11
191	Observation of the valence-subband level crossing in GaAs/GaAsP strained-barrier quantum well structures using circularly polarized photoluminescence excitation spectroscopy. <i>Applied Physics Letters</i> , 1993, 63, 946-948.	3.3	6
192	Two-dimensional exciton dynamics in InGaAs/GaAs quantum wells. <i>Applied Physics Letters</i> , 1992, 60, 213-215.	3.3	15
193	Anomalies in photoluminescence linewidth of InGaAs/GaAs strained-layer quantum wells. <i>Surface Science</i> , 1992, 267, 107-109.	1.9	14
194	Surface segregation of In atoms during molecular beam epitaxy and its influence on the energy levels in InGaAs/GaAs quantum wells. <i>Applied Physics Letters</i> , 1992, 61, 557-559.	3.3	450
195	Bidirectional Current Drag Induced by Two-Electron Cotunneling in Coupled Double Quantum Dots. <i>Applied Physics Express</i> , 0, 2, 081101.	2.4	21